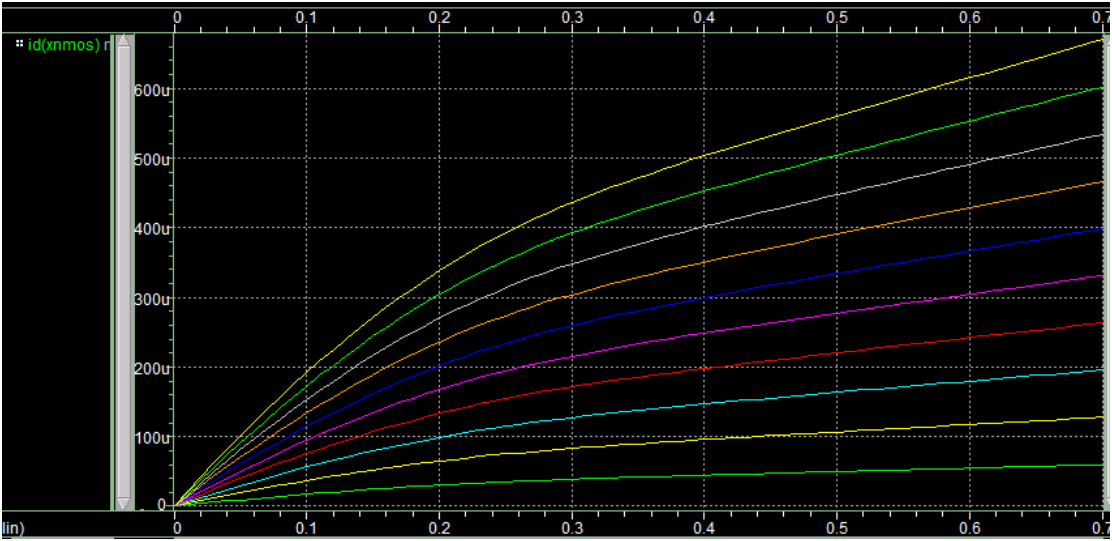
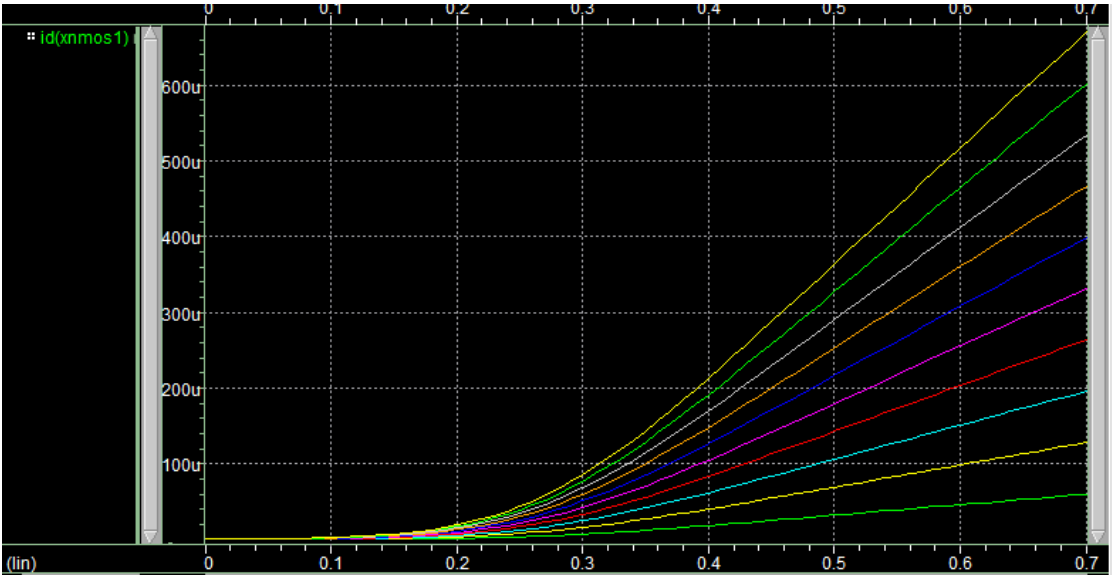


1、IV 曲线展示

n-channel bulk Si-MOSFET,  $I_{ds}$ - $V_{ds}$  @25°C,  $V_{gs}=0.7V$ , width=3 $\lambda$ -30 $\lambda$ :



n-channel bulk Si-MOSFET,  $I_{ds}$ - $V_{gs}$  @25°C,  $V_{ds}=0.7V$ , width=3 $\lambda$ -30 $\lambda$ :



2、测量数据表格

Measure@25°C, n-channel bulk Si-MOSFET:

Width	3 $\lambda$	6 $\lambda$	9 $\lambda$	12 $\lambda$	15 $\lambda$
$I_{on}$ (uA)	59.83 (示例数据, 建议数据保留两位小数)				
$I_{off}$ (nA)	18.22				
$I_{on}/I_{off}$ ( $\times 10^3$ )	3.28				
$R_{on}/R_{off}$ ( $\times 10^3$ )					
Subthreshold Slope (mV/dec)					

Measure@25°C, p-channel bulk Si-MOSFET:

Width	3 $\lambda$	6 $\lambda$	9 $\lambda$	12 $\lambda$	15 $\lambda$
I <sub>on</sub> (uA)					
I <sub>off</sub> (nA)					
I <sub>on</sub> /I <sub>off</sub> (x10 <sup>3</sup> )					
R <sub>on</sub> /R <sub>off</sub> (x10 <sup>3</sup> )					
Subthreshold Slope (mV/dec)					

Measure@25°C, n-channel FinFET:

Fin number	1	2	3	4	5
W <sub>eff</sub> (nm)					
I <sub>on</sub> (uA)					
I <sub>off</sub> (nA)					
I <sub>on</sub> /I <sub>off</sub> (x10 <sup>3</sup> )					
R <sub>on</sub> /R <sub>off</sub>					
Subthreshold Slope (mV/dec)					
Width	6	7	8	9	10
W <sub>eff</sub> (nm)					
I <sub>on</sub> (uA)					
I <sub>off</sub> (nA)					
I <sub>on</sub> /I <sub>off</sub> (x10 <sup>3</sup> )					
R <sub>on</sub> /R <sub>off</sub> (x10 <sup>3</sup> )					
Subthreshold Slope (mV/dec)					

Measure@25°C, p-channel FinFET:

Fin number	1	2	3	4	5
W <sub>eff</sub> (nm)					
I <sub>on</sub> (uA)					
I <sub>off</sub> (nA)					

<b>I<sub>on</sub>/I<sub>off</sub> (x10<sup>3</sup>)</b>					
<b>R<sub>on</sub>/R<sub>off</sub> (x10<sup>3</sup>)</b>					
<b>Subthreshold Slope (mV/dec)</b>					
<b>Width</b>	<b>6</b>	<b>7</b>	<b>8</b>	<b>9</b>	<b>10</b>
<b>W<sub>eff</sub> (nm)</b>					
<b>I<sub>on</sub> (uA)</b>					
<b>I<sub>off</sub> (nA)</b>					
<b>I<sub>on</sub>/I<sub>off</sub> (x10<sup>3</sup>)</b>					
<b>R<sub>on</sub>/R<sub>off</sub> (x10<sup>3</sup>)</b>					
<b>Subthreshold Slope (mV/dec)</b>					

Measure@25°C, n-channel TFET (**Optional**):

<b>Width</b>	<b>3λ</b>	<b>6λ</b>	<b>9λ</b>	<b>12λ</b>	<b>15λ</b>
<b>I<sub>on</sub> (uA)</b>					
<b>I<sub>off</sub> (nA)</b>					
<b>I<sub>on</sub>/I<sub>off</sub> (x10<sup>3</sup>)</b>					
<b>R<sub>on</sub>/R<sub>off</sub> (x10<sup>3</sup>)</b>					
<b>Subthreshold Slope (mV/dec)</b>					

Measure@25°C, p-channel TFET (**Optional**):

<b>Width</b>	<b>3λ</b>	<b>6λ</b>	<b>9λ</b>	<b>12λ</b>	<b>15λ</b>
<b>I<sub>on</sub> (uA)</b>					
<b>I<sub>off</sub> (nA)</b>					
<b>I<sub>on</sub>/I<sub>off</sub> (x10<sup>3</sup>)</b>					
<b>R<sub>on</sub>/R<sub>off</sub> (x10<sup>3</sup>)</b>					
<b>Subthreshold Slope (mV/dec)</b>					